

# Application of hydrogen-reduction to improve ceria slurry performance on chemical mechanical polishing process

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Ceria slurry is widely used in the dielectric CMP (chemical mechanical polishing) process due to its advantages of high polishing performance and selectivity.  $\text{Ce}^{3+}$  ions on the ceria surface form a Ce-O-Si bond with the  $\text{SiO}_2$  wafer, which contributing to polishing performance [1]. In this study, we increased the  $\text{Ce}^{3+}$  concentration by using the hydrogen-reduction method and performed CMP evaluated using the reduced ceria slurry.

Figure 1 shows the process of ceria reduction in a high-temperature hydrogen atmosphere. Hydrogen-reduction begins with the penetration of hydrogen into ceria and adsorption to oxygen to form hydroxyl. The generated hydroxyls react with hydrogen to induce  $\text{H}_2\text{O}$  molecular desorption, and which generates oxygen vacancies. In this study, we optimized the hydrogen-reduction conditions and evaluated the reduced ceria slurries according to the reduction temperature.

Figure 2 shows the  $\text{Ce}^{3+}$  concentration and polishing performance according to the reduction temperature. It was evaluated that the reduction of ceria was not sufficiently performed under a relatively low temperature condition. The hydrogen-reduction reaction increased significantly with a constant temperature, and the same tendency was observed in the polishing performance. Based on the above, it was evaluated that the concentration of  $\text{Ce}^{3+}$  increased as the reduction temperature increased, and which had a direct effect on the increase of polishing performance.

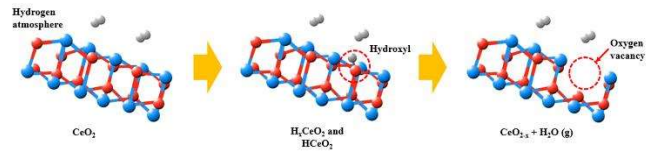


Fig.1 Schematic of ceria hydrogen-reduction.

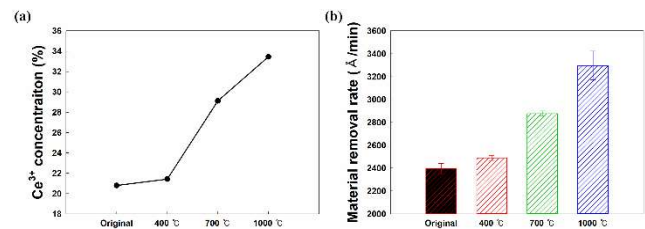


Fig.2  $\text{Ce}^{3+}$  concentration and polishing performance of ceria slurries.

## Reference

- [1] K. Kim, D.K. Yi, U. Paik, Increase in  $\text{Ce}^{3+}$  concentration of ceria nanoparticles for high removal rate of  $\text{SiO}_2$  in chemical mechanical planarization, ECS Journal of Solid State Science and Technology 6(9) (2017) P681.
- [2] T. Matsukawa, A. Hoshikawa, E. Niwa, M. Yashima, T. Ishigaki, Crystal structure of blue-colored ceria during redox reactions in a hydrogen atmosphere, CrystEngComm 20(2) (2018) 155-158.

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